



## Future Normal in Semiconductor

2025년 2월 14일(금), 09:00-10:45

Room I(스페이드 I), 6층

P. Device for Energy (Solar Cell, Power Device, Battery, etc.) 분과

### 049\_[F11-P] Power Device

좌장: 차호영 교수(홍익대학교), 홍영준 교수(성균관대학교)

초청 F11-P-1 09:00-09:30	<b>Gallium Nitride Power Semiconductor Devices</b> Ho-Young Cha <sup>1,2</sup> <sup>1</sup> Hongik University, <sup>2</sup> CHIPSK
F11-P-2 09:30-09:45	<b>Enhancing BeO Electric Properties on 4H-SiC with SiO<sub>2</sub> Interlayer for Power Device Applications</b> Sangoh Han <sup>1,2</sup> , Juyoung chae <sup>1,2</sup> , Jonghyun Bae <sup>1,2</sup> , Dohwan Jung <sup>1</sup> , Siwon Lee <sup>3</sup> , and Jungwoo Oh <sup>1,2</sup> <sup>1</sup> School of Integrated Technology, Yonsei University, <sup>2</sup> BK21 Graduate Program in Intelligent Semiconductor Technology, Yonsei University, <sup>3</sup> Nano Science and Engineering, Yonsei University
F11-P-3 09:45-10:00	<b>Self-Aligned 플라즈마 처리를 통한 NiO/<math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> 이종 접합 파워다이오드의 질소 도핑</b> 김동빈 <sup>1</sup> , 백종수 <sup>1</sup> , 최윤호 <sup>1</sup> , 김형우 <sup>2</sup> , 조병진 <sup>1</sup> <sup>1</sup> 한국과학기술원 전기및전자공학부, <sup>2</sup> 한국전기연구원 전력반도체연구단
F11-P-4 10:00-10:15	<b>Eco-Friendly Power Sources for Interactive Sensor-Embedded Displays Using Transient Battery Technology</b> Hyeonbin Jo, Mukurala Nagaraju, Geun Lee, Hyeon Hong Lee, Hanmin Kim, and Sung Hun Jin Incheon National University
F11-P-5 10:15-10:30	<b>Transferred Graphene Monolayer for <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Based Power Devices Applications</b> Madani Labeled <sup>1,2</sup> , Bo-In Park <sup>3,4</sup> , Jekyung Kim <sup>3,4</sup> , Jang Hyeok Park <sup>1,2</sup> , Jeehwan Kim <sup>3,4</sup> , and You Seung Rim <sup>1,2</sup> <sup>1</sup> Department of Semiconductor Systems Engineering and Convergence Engineering for Intelligent Drone, Sejong University, <sup>2</sup> Institute of Semiconductor and System IC, Sejong University, <sup>3</sup> Department of Mechanical Engineering, Massachusetts Institute of Technology, USA, <sup>4</sup> Research Laboratory of Electronics, Massachusetts Institute of Technology, USA



# 제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

## *Future Normal in Semiconductor*

F11-P-6

10:30-10:45

이온 주입 공정을 활용한 다이아몬드 기반 쇼트키 장벽 다이오드

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